

HEWLETT-PACKARD COMPA Intellectual Property Administration P. O. Box 272400 Fort Collins, Colorado 80527-2400

PATENT APPLICATION

ATTORNEY DOCKET NO. 10981967-2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor(s):

Philip J. Kuekes et al

Confirmation No.:

Application No.: 09/280,188

Examiner: D.A. Wille

Filing Date:

March 29, 1999

Group Art Unit: 2814

Title:

MOLECULAR WIRE TRANSISTORS (MWT)

EV075984904US

COMMISSIONER FOR PATENTS Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT

Sir:

This Information Disclosure Statement is submitted:

- () under 37 CFR 1.97(b), or
 - (Within three months of filing national application; or date of entry of national application; or before mailing date of first office action on the merits; whichever occurs last)
- (X) under 37 CFR 1.97(c) together with either a:
 - () Statement under 37 CFR 1.97(e), or
 - (X) a \$180.00 fee under 37 CFR 1.17(p), or

(After the CFR 1.97 (b) time period, but before final action or notice of allowance, whichever occurs

- () under 37 CFR 1.97 (d) together with a:
 - () Statement under 37 CFR 1.97(e), and
 - () a petition under 37 CFR 1.97(d)(2), and
 - () a \$180.00 petition fee set forth in 37 CFR 1.17(p).

(Filed after final action or notice of allowance, whichever occurs first, but before payment of the issue fee)

Please charge to Deposit Account 08-2025 the sum of \$180.00 . At any time during the pendency of this application, please charge any fees required or credit any overpayment to Deposit Account 08-2025 pursuant to 37 CFR 1.25.

- (X) Applicant(s) submit herewith Form PTO 1449 - Information Disclosure Citation together with copies, of patents, publications or other information of which applicant(s) are aware, which applicant(s) believe(s) may be material to the examination of this application and for which there may be a duty to disclose in accordance with 37 CFR 1.56.
- A concise explanation of the relevance of foreign language patents, foreign language publications and other foreign language information listed on PTO Form 1449, as presently understood by the individuals(s) designated in 37 CFR 1.56 (c) most knowledgeable about the content is given on the attached sheet, or where a foreign language patent is cited in a search report or other action by a foreign patent office in a counterpart foreign application, an English language version of the search report or action which indicates the degree of relevance found by the foreign office is listed on form PTO 1449 and is enclosed herewith.

It is requested that the information disclosed herein be made of record in this application.

"Express Mail" label no.EV 075984904

Date of Deposit April 15, 2002

I hereby certify that this is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to: Commissioner for Patents, Washington,

By Muka Best Christock

Respectfully submitted,

Philip J. Kuekes et al

David W. Collins

Attorney/Agent for Applicant(s)



Sheet 1 of 5

FORM PTO-1449

LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

| ATTY. DOCKET NO. | | SERIAL NO. |
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REFERENCE DESIGNATION

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